



- (51) **International Patent Classification:**  
*H01L 25/07* (2006.01) *H01L 23/538* (2006.01)
- (21) **International Application Number:**  
PCT/US2023/077083
- (22) **International Filing Date:**  
17 October 2023 (17.10.2023)
- (25) **Filing Language:** English
- (26) **Publication Language:** English
- (30) **Priority Data:**  
63/379,853 17 October 2022 (17.10.2022) US  
18/487,835 16 October 2023 (16.10.2023) US
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(81) **Designated States** (*unless otherwise indicated, for every kind of national protection available*): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, MG, MK, MN, MU, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) **Designated States** (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, CV, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SC, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, ME, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

(54) **Title:** ASSEMBLIES WITH EMBEDDED SEMICONDUCTOR DEVICE MODULES AND RELATED METHODS

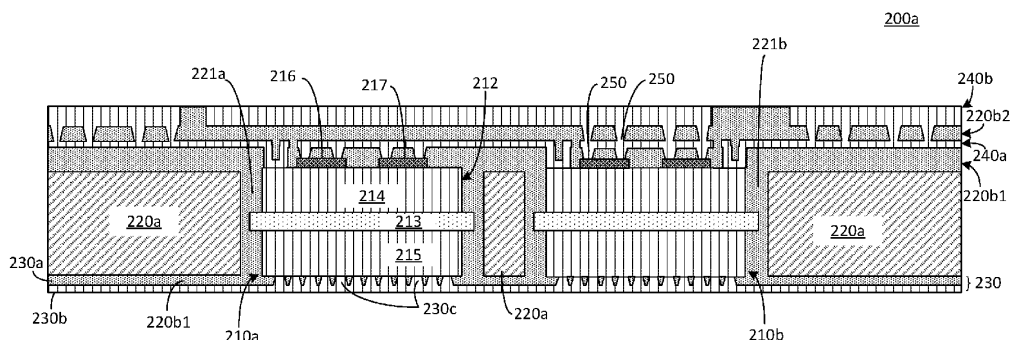


FIG. 2A

(57) **Abstract:** In a general aspect, an assembly (200a) includes a panel of organic substrate core material (220a) having a cavity (221a, 221b) defined therein, a module substrate (212) disposed in the cavity, and a semiconductor die (216, 217) disposed on the module substrate. The assembly also includes a layer of prepreg organic substrate material (220b1), and a metal layer (240a). The module substrate and the semiconductor die are embedded in the cavity by the layer of prepreg organic substrate material and the metal layer. The metal layer is electrically coupled with at least one of the semiconductor die or the module substrate.

[Continued on next page]

**Published:**

- *with international search report (Art. 21(3))*
- *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments (Rule 48.2(h))*